





#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- **ESD Protected Gate**
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

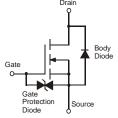
- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.001 grams (approximate)











Internal Schematic **Equivalent Circuit** 

### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	V <sub>GSS</sub>	±10	V
Drain Current per element (Note 1)	I <sub>D</sub>	440	mA

#### Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	$P_{D}$	450	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	218	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-65 to +150	°C

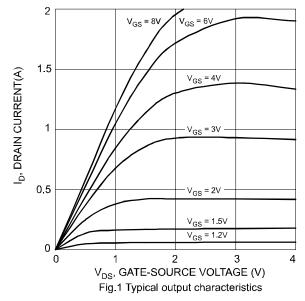
# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

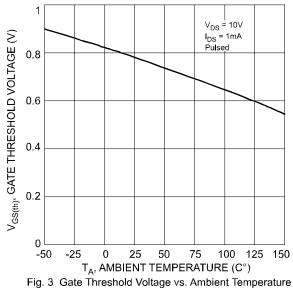
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)			•		•	•
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_		V	$V_{GS} = 0V, I_D = 100 \mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	10	μА	V <sub>DS</sub> = 17V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±5	μА	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.53	_	1.2	V	$V_{DS} = V_{GS}$ , $I_D = 100 \mu A$
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)		1.2 1.3 1.2 2.4 2.5	1.5 1.7 1.7 3.5 3.5	Ω	$V_{GS} = 4V, I_D = 10mA$ $V_{GS} = 2.7V, I_D = 200mA$ $V_{GS} = 2.5V, I_D = 10mA$ $V_{GS} = 1.8V, I_D = 200mA$ $V_{GS} = 1.5V, I_D = 1mA$
Forward Transfer Admittance	Y <sub>fs</sub>	40	_	_	mS	$V_{DS} = 3V$ , $I_D = 10mA$

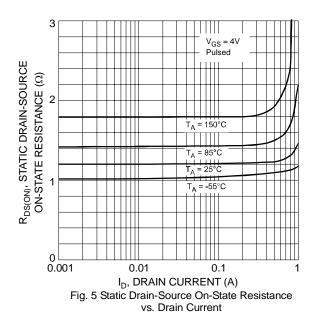
Notes:

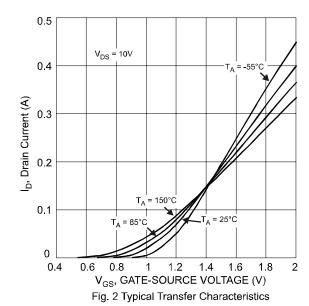
- Device mounted on FR-4 PCB.
- 2. No purposefully added lead
- Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php
- 4. Short duration pulse test used to minimize self-heating effect.

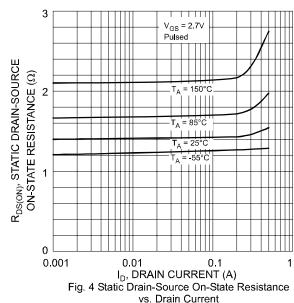












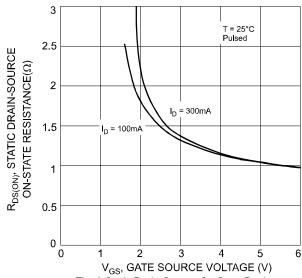


Fig. 6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

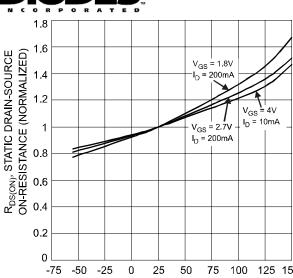
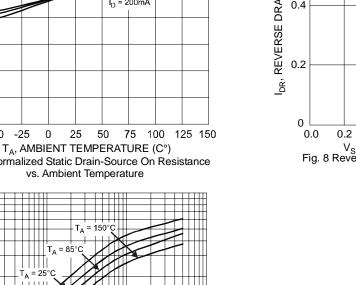


Fig. 7 Normalized Static Drain-Source On Resistance vs. Ambient Temperature



In, DRAIN CURRENT (A) Fig. 9 Forward Transfer Admittance vs. Drain Current

0.01

# 8.0 I<sub>DR</sub>, REVERSE DRAIN CURRENT (A) 0.6 $T_A = 150^{\circ}C$ = 85°C T<sub>Δ</sub> = -55°C 0.6 8.0 $\rm V_{SD}$ , SOURCE-DRAIN VOLTAGE (V) Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

## Ordering Information (Note 5)

Part Number	Case	Packaging
DMN2005LPK-7	DFN1006-3	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

0.1

# **Marking Information**

0.001

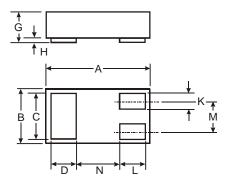
|Y<sub>fs</sub>|, FORWARD TRANSFER ADMITTANCE, (S) 0.1

DM

DM = Product Type Marking Code Dot Denotes Drain Side

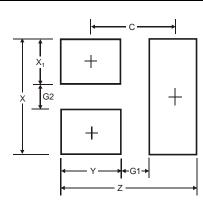


## **Package Outline Dimensions**



	DFN1006-3				
Dim	Min	Max	Тур		
Α	0.95	1.075	1.00		
В	0.55	0.675	0.60		
С	0.45	0.55	0.50		
D	0.20	0.30	0.25		
G	0.47	0.53	0.50		
Η	0	0.05	0.03		
K	0.10	0.20	0.15		
L	0.20	0.30	0.25		
М			0.35		
N			0.40		
All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
С	0.7

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